NSN 5961-01-333-8518

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-333-8518 **Inclosure Material:** Metal and glass **Overall Length:** 44.5 millimeters **End Application:** 5865-01-188-3309 jamming system, communications, general utility **Mounting Facility Quantity:** 1 **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 16.95 millimeters and 17.47 millimeters Thread Size: 0.250 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 150.0 nonrepetitive peak off-state voltage and 150.0 nonrepetitive peak reverse voltage and 100.0 repetitive peak off-state voltage and 100.0 repetitive peak reverse voltage and 100.0 working peak off-state voltage and 100.0 working peak reverse voltage **Current Rating Per Characteristic:** 33.00 amperes drain current universal and 50.00 amperes drain current pascal **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 135.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: